

# 2N2484, 2N2484UA, 2N2484UB

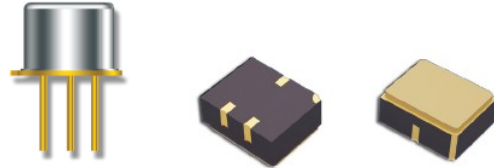


## NPN Low Power Silicon Transistor

Rev. V1

### Features

- JANS Qualified to MIL-PRF-19500/376
- JEDEC registered 2N2484
- Lightweight & Low Power
- Military & other High Reliability Applications
- TO-18 (TO-206AA), TO-46 (TO-206AB) Surface Mount UA, UB Package Styles



### Electrical Characteristics

Parameter	Test Conditions	Symbol	Units	Min.	Max.
<b>Off Characteristics</b>					
Collector - Emitter Breakdown Voltage	$I_C = 10 \text{ mA}$	$V_{(BR)CEO}$	Vdc	60	—
Collector - Emitter Cutoff Current	$V_{CE} = 45 \text{ Vdc}$	$I_{CES}$	nAdc	—	5
Collector - Base Cutoff Current	$V_{CB} = 45 \text{ Vdc}$ $V_{CB} = 60 \text{ Vdc}$	$I_{CBO}$	nAdc $\mu\text{Adc}$	—	5 10
Collector - Emitter Cutoff Current	$V_{CE} = 5 \text{ Vdc}$	$I_{EBO}$	nAdc	—	2
<b>On Characteristics<sup>1</sup></b>					
Forward Current Transfer Ratio	$I_C = 1 \mu\text{Adc}, V_{CE} = 5 \text{ Vdc}$ $I_C = 10 \mu\text{Adc}, V_{CE} = 5 \text{ Vdc}$ $I_C = 100 \mu\text{Adc}, V_{CE} = 5 \text{ Vdc}$ $I_C = 500 \mu\text{Adc}, V_{CE} = 5 \text{ Vdc}$ $I_C = 1 \text{ mAdc}, V_{CE} = 5 \text{ Vdc}$ $I_C = 10 \text{ mAdc}, V_{CE} = 5 \text{ Vdc}$	$H_{FE}$	-	45 200 225 250 250 225	— 500 675 800 800 800
Collector - Emitter Saturation Voltage	$I_C = 1 \text{ mAdc}, I_B = 100 \mu\text{Adc}$	$V_{CE(SAT)}$	Vdc	—	0.3
Base - Emitter Saturation Voltage	$I_C = 5 \text{ mAdc}, I_B = 100 \mu\text{Adc}$	$V_{BE(SAT)}$	Vdc	0.5	0.7
<b>Dynamic Characteristics</b>					
Forward Current Transfer Ratio	$I_C = 50 \mu\text{Adc}, V_{CE} = 5 \text{ Vdc}, 5 \text{ MHz}$ $I_C = 500 \mu\text{Adc}, V_{CE} = 5 \text{ Vdc}, 30 \text{ MHz}$	$ h_{FE} $	-	3.0 2.0	— 0.7
Open Circuit Output Admittance	$I_C = 10 \text{ mAdc}, V_{CE} = 5 \text{ Vdc}, f = 1 \text{ kHz}$	$h_{OE}$	$\mu\text{mhos}$	—	40
Open Circuit Reverse Voltage Transfer Ratio	$I_C = 10 \text{ mAdc}, V_{CE} = 5 \text{ Vdc}, f = 1 \text{ kHz}$	$h_{RE}$	-	—	$8 \times 10^{-4}$
Input Impedance	$I_C = 10 \text{ mAdc}, V_{CE} = 5 \text{ Vdc}, f = 1 \text{ kHz}$	$h_{iE}$	k $\Omega$	3.5	24.0
Small-Signal Short-Circuit Forward Current Transfer Ratio	$I_C = 10 \text{ mAdc}, V_{CE} = 5 \text{ Vdc}, f = 1 \text{ kHz}$	$h_{FE}$	-	250	900
Output Capacitance	$V_{CB} = 5 \text{ V}, I_E = 0, 100 \text{ kHz} \leq f \leq 1 \text{ MHz}$	$C_{OBO}$	pF	—	5
Input Capacitance	$V_{EB} = 5 \text{ V}, I_E = 0, 100 \text{ kHz} \leq f \leq 1 \text{ MHz}$	$C_{IBO}$	pF	—	6

1. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

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### Absolute Maximum Ratings

Ratings	Symbol	Value
Collector - Emitter Voltage	$V_{CEO}$	60 Vdc
Collector - Base Voltage	$V_{CBO}$	60 Vdc
Emitter - Base Voltage	$V_{EBO}$	6 Vdc
Collector Current	$I_C$	50 mAdc
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_T$	360 W
Operating & Storage Temperature Range	$T_{OP}, T_{STG}$	$-65^\circ\text{C}$ to $+200^\circ\text{C}$

### Thermal Characteristics

Characteristics	Symbol	Max. Value
Thermal Resistance, Junction to Ambient 2N2484 2N2484UA 2N2484UB, UBC	$R_{\theta JA}$	325°C/W 275°C/W 350°C/W

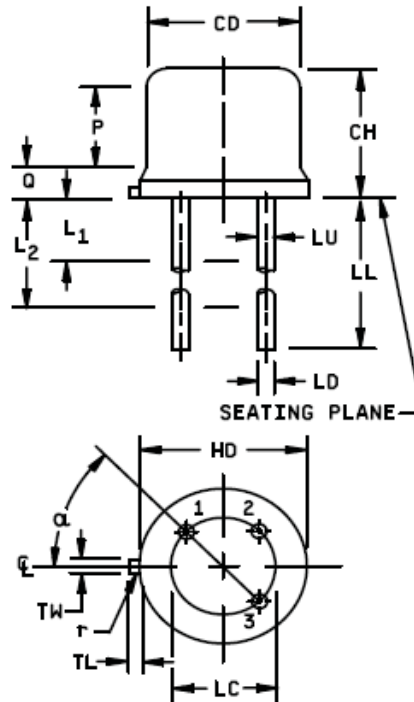
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## Outline Drawing (TO-18)



### NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Beyond  $r$  (radius) maximum, TL shall be held for a minimum length of .011 inch (0.28 mm).
4. Dimension TL measured from maximum HD.
5. Body contour optional within zone defined by HD, CD, and Q.
6. Leads at gauge plane  $.054 +.001 -0.000$  inch ( $1.37 +0.03 -0.00$  mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC.
7. Dimension LU applies between  $L_1$  and  $L_2$ . Dimension LD applies between  $L_2$  and LL minimum. Diameter is uncontrolled in  $L_1$  and beyond LL minimum.
8. All three leads.
9. The collector shall be internally connected to the case.
10. Dimension  $r$  (radius) applies to both inside corners of tab.
11. In accordance with ASME Y14.5M, diameters are equivalent to  $\phi x$  symbology.
12. Lead 1 = emitter, lead 2 = base, lead 3 = collector.
13. For L suffix devices, dimension LL = 1.5 inches (38.10 mm) min. and 1.75 inches (44.45 mm) max.

Symbol	Dimensions				Note
	Inches		Millimeters		
	Min	Max	Min	Max	
CD	.178	.195	4.52	4.95	
CH	.170	.210	4.32	5.33	
HD	.209	.230	5.31	5.84	
LC	.100 TP		2.54 TP		6
LD	.016	.021	0.41	0.53	7,8
LL	.500	.750	12.70	19.05	7,8,13
LU	.016	.019	0.41	0.48	7,8
$L_1$		.050		1.27	7,8
$L_2$	.250		6.35		7,8
P	.100		2.54		
Q		.030		0.76	5
TL	.028	.048	0.71	1.22	3,4
TW	.036	.046	0.91	1.17	3
$r$		.010		0.25	10
$\alpha$	45° TP		45° TP		6
1, 2, 9, 11, 12, 13					

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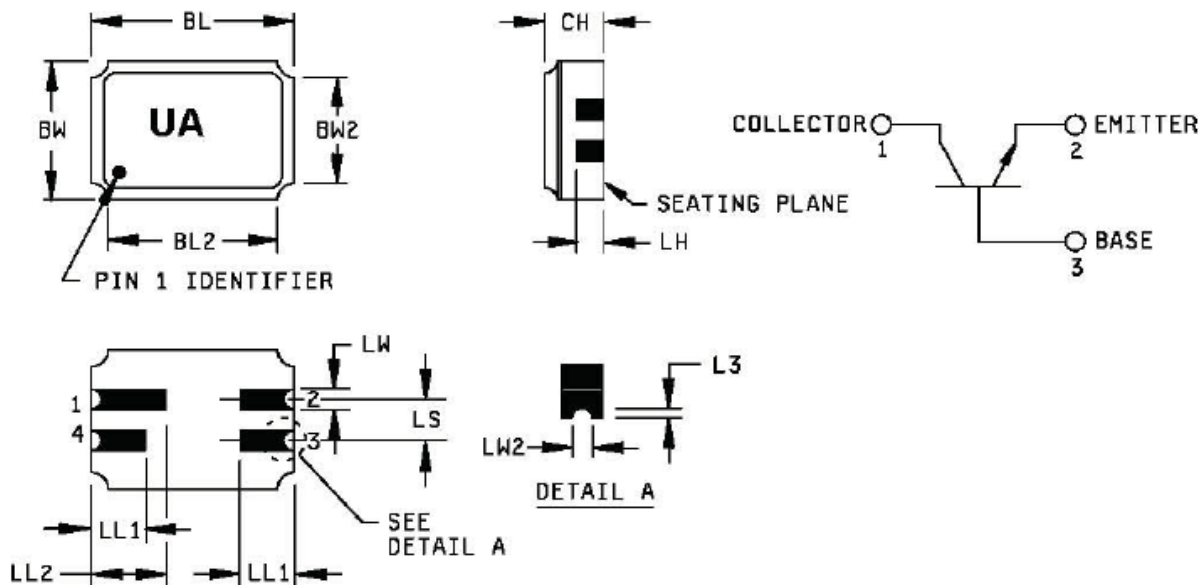
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### Outline Drawing (UA Surface Mount)



#### NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Dimension CH controls the overall package thickness. When a window lid is used, dimension CH must increase by a minimum of .010 inch (0.254 mm) and a maximum of .040 inch (1.020 mm).
4. The corner shape (square, notch, radius) may vary at the manufacturer's option, from that shown on the drawing.
5. Dimensions LW2 minimum and L3 minimum and the appropriate castellation length define an unobstructed three-dimensional space traversing all of the ceramic layers in which a castellation was designed. (Castellations are required on the bottom two layers, optional on the top ceramic layer.) Dimension LW2 maximum and L3 maximum define the maximum width and depth of the castellation at any point on its surface. Measurement of these dimensions may be made prior to solder dipping.
6. The co-planarity deviation of all terminal contact points, as defined by the device seating plane, shall not exceed .006 inch (0.15mm) for solder dipped leadless chip carriers.
7. In accordance with ASME Y14.5M, diameters are equivalent to  $\phi x$  symbology.

Symbol	Dimensions				Note
	Inches		Millimeters		
	Min	Max	Min	Max	
BL	.215	.225	5.46	5.71	
BL2		.225		5.71	
BW	.145	.155	3.68	3.93	
BW2		.155		3.93	
CH	.061	.075	1.55	1.90	3
L3	.003	.007	0.08	0.18	5
LH	.029	.042	0.74	1.07	
LL1	.032	.048	0.81	1.22	
LL2	.072	.088	1.83	2.23	
LS	.045	.055	1.14	1.39	
LW	.022	.028	0.56	0.71	
LW2	.006	.022	0.15	0.56	5

Pin no.	1	2	3	4
Transistor	Collector	Emitter	Base	N/C

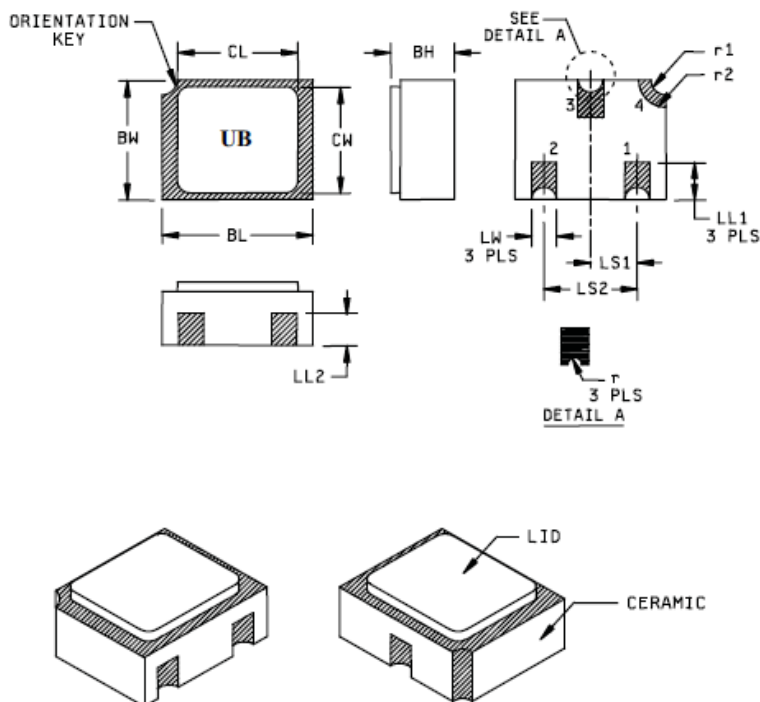
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## Outline Drawing (UB, UBC\* (\*ceramic lid version) Surface Mount)



Symbol	Dimensions				Note
	Inches		Millimeters		
	Min	Max	Min	Max	
BH	.046	.056	1.17	1.42	
BL	.115	.128	2.92	3.25	
BW	.085	.108	2.16	2.74	
CL		.128		3.25	
CW		.108		2.74	
LL1	.022	.038	0.56	0.96	
LL2	.017	.035	0.43	0.89	

Symbol	Dimensions				Note
	Inches		Millimeters		
	Min	Max	Min	Max	
LS <sub>1</sub>	.036	.040	0.91	1.02	
LS <sub>2</sub>	.071	.079	1.81	2.01	
LW	.016	.024	0.41	0.61	
r		.008		.203	
r <sub>1</sub>		.012		.305	
r <sub>2</sub>		.022		.559	

### NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Hatched areas on package denote metalized areas.
4. Pad 1 = Base, Pad 2 = Emitter, Pad 3 = Collector, Pad 4 = Shielding connected to the lid.
5. In accordance with ASME Y14.5M, diameters are equivalent to  $\phi x$  symbology.

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